Dual NPN Bias Resistor Transistors R1 = 4.7 kΩ, R2 = ∞ kΩ

NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

(T_A = 25°C, common for Q1 and Q2, unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current - Continuous	I _C	100	mAdc
Input Forward Voltage	$V_{IN(fwd)}$	30	Vdc
Input Reverse Voltage	V _{IN(rev)}	6	Vdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ORDERING INFORMATION

Device	Package	Shipping [†]
MUN5216DW1T1G, SMUN5216DW1T1G	SOT-363	3,000 / Tape & Reel
NSBC143TDXV6T1G	SOT-563	4,000 / Tape & Reel
NSBC143TDXV6T5G	SOT-563	8,000 / Tape & Reel

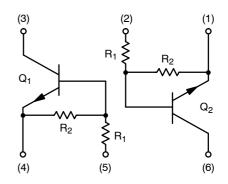
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



ON Semiconductor®

http://onsemi.com

PIN CONNECTIONS



MARKING DIAGRAMS





SOT-363 CASE 419B





SOT-563 CASE 463A

7F = Specific Device Code

M = Date Code*

• Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

THERMAL CHARACTERISTICS

MUN5216DW1 (SOT-363) One Junction Heated Total Device Dissipation TA = 25°C (Note (e 2) e 1) e 2)	P _D	187 256 1.5 2.0 670 490	mW mW/°C
$T_{A} = 25^{\circ}\text{C} \qquad \qquad (Not (Not (Not (Not (Not (Not (Not (Not $	e 2) e 1) e 2)		256 1.5 2.0 670	mW/°C
Junction to Ambient (Note MUN5216DW1 (SOT-363) Both Junction Heated (Note 3) Total Device Dissipation T _A = 25°C (Note Derate above 25°C (Note (Note)		$R_{ hetaJA}$		°C/W
Total Device Dissipation $T_A = 25^{\circ}C \hspace{1cm} \text{(Not } \\ \text{(Not } \\ \text{Derate above } 25^{\circ}C \hspace{1cm} \text{(Not } \\ \text{(Not }$				<u>,</u>
T _A = 25°C (Note Note Derate above 25°C) (Note Note Note Note Note Note Note Note				
Thermal Resistance, (Not	e 2) e 1)	P_D	250 385 2.0 3.0	mW mW/°C
Junction to Ambient (Not		R_{\thetaJA}	493 325	°C/W
Thermal Resistance, Junction to Lead (Note		$R_{ hetaJL}$	188 208	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C
NSBC143TDXV6 (SOT-563) One Junction Heated				
Total Device Dissipation T _A = 25°C (Note Derate above 25°C (Note December 25°C)		P _D	357 2.9	mW mW/°C
Thermal Resistance, Junction to Ambient (Note	e 1)	$R_{\theta JA}$	350	°C/W
NSBC143TDXV6 (SOT-563) Both Junction Heated (Note 3)				
Total Device Dissipation T _A = 25°C (Note Derate above 25°C (Note December 25°C)		P _D	500 4.0	mW mW/°C
Thermal Resistance, Junction to Ambient (Note	e 1)	$R_{ hetaJA}$	250	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}		°C

FR-4 @ Minimum Pad.
 FR-4 @ 1.0 x 1.0 Inch Pad.
 Both junction heated values assume total power is sum of two equally powered channels.

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C, common for Q_1 and Q_2 , unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•	-		
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I _{CBO}	_	_	100	nAdc
Collector-Emitter Cutoff Current (V _{CE} = 50 V, I _B = 0)	I _{CEO}	_	_	500	nAdc
Emitter-Base Cutoff Current (V _{EB} = 6.0 V, I _C = 0)	I _{EBO}	-	-	1.9	mAdc
Collector–Base Breakdown Voltage ($I_C = 10 \mu A, I_E = 0$)	V _(BR) CBO	50	_	-	Vdc
Collector-Emitter Breakdown Voltage (Note 4) (I _C = 2.0 mA, I _B = 0)	V _(BR) CEO	50	_	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 4) (I _C = 5.0 mA, V _{CE} = 10 V)	h _{FE}	160	350	-	
Collector–Emitter Saturation Voltage (Note 4) (I _C = 10 mA, I _B = 1.0 mA)	V _{CE(sat)}	_	_	0.25	Vdc
Input Voltage (off) $(V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A})$	V _{i(off)}	_	0.6	-	Vdc
Input Voltage (on) (V _{CE} = 0.2 V, I _C = 10 mA)	V _{i(on)}	_	0.9	-	Vdc
Output Voltage (on) $(V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V _{OL}	-	-	0.2	Vdc
Output Voltage (off) $(V_{CC} = 5.0 \text{ V}, V_B = 0.25 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V _{OH}	4.9	_	-	Vdc
Input Resistor	R1	3.3	4.7	6.1	kΩ
Resistor Ratio	R ₁ /R ₂	-	-	-	

^{4.} Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

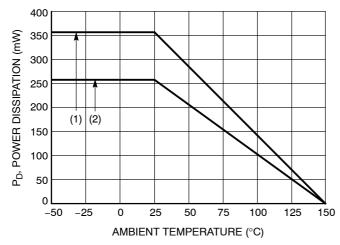


Figure 1. Derating Curve

- (1) SOT-363; 1.0×1.0 inch Pad
- (2) SOT-563; Minimum Pad

TYPICAL CHARACTERISTICS MUN5216DW1, NSBC143TDXV6

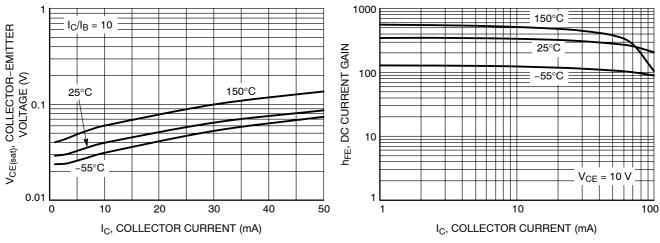


Figure 2. V_{CE(sat)} vs. I_C

Figure 3. DC Current Gain

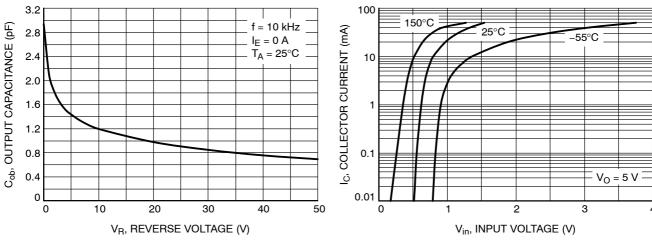


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

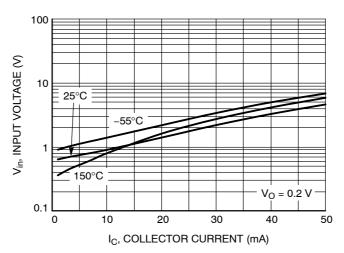
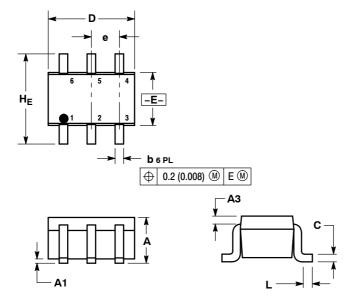


Figure 6. Input Voltage vs. Output Current

PACKAGE DIMENSIONS

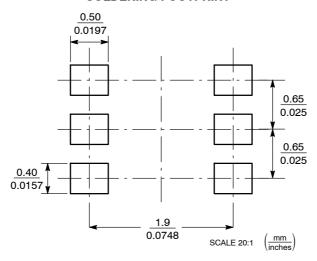
SC-88/SC70-6/SOT-363 CASE 419B-02 **ISSUE W**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	MIL	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX		
Α	0.80	0.95	1.10	0.031	0.037	0.043		
A1	0.00	0.05	0.10	0.000	0.002	0.004		
А3	0.20 REF			0.008 REF				
b	0.10	0.21	0.30	0.004	0.008	0.012		
С	0.10	0.14	0.25	0.004	0.005	0.010		
D	1.80	2.00	2.20	0.070	0.078	0.086		
Е	1.15	1.25	1.35	0.045	0.049	0.053		
е	0.65 BSC			0.026 BSC				
L	0.10	0.20	0.30	0.004	0.008	0.012		
He	2.00	2.10	2.20	0.078	0.082	0.086		

SOLDERING FOOTPRINT*

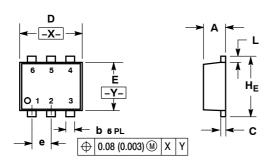


SC-88/SC70-6/SOT-363

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A ISSUE F

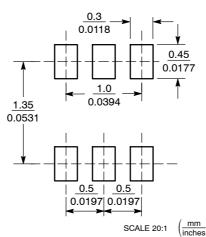


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD
 FINISH THICKNESS. MINIMUM LEAD THICKNESS
 IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
Е	1.10	1.20	1.30	0.043	0.047	0.051
е	0.5 BSC			C	.02 BS0	
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.50	1.60	1.70	0.059	0.062	0.066

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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